

isc Silicon PNP Power Transistors

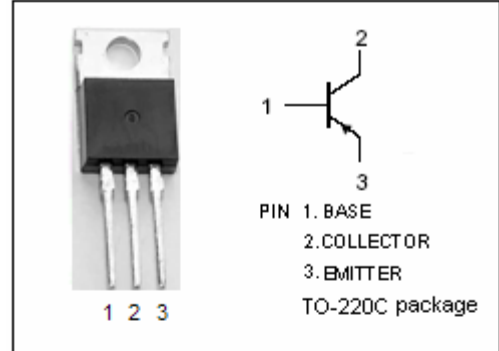
D45H Series

DESCRIPTION

- Low Saturation Voltage
- Fast Switching Speeds
- Complement to Type D44H Series

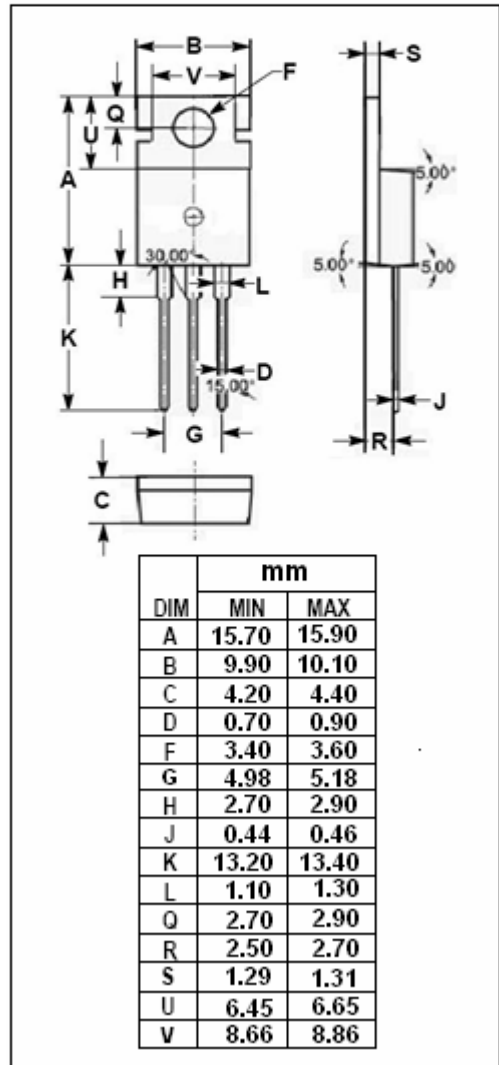
APPLICATIONS

- Designed for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifier.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CEO}	Collector-Emitter Voltage	D45H8	-60	V
		D45H10,11	-80	
V _{EBO}	Emitter-Base Voltage	-5	V	
I _C	Collector Current-Continuous	-10	A	
I _{CM}	Collector Current-Peak	-20	A	
P _C	Collector Power Dissipation @T _C =25°C	-50	W	
T _j	Junction Temperature	150	°C	
T _{stg}	Storage Temperature Range	-55~150	°C	



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.5	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	75	°C/W

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	D44H10	I _C = -8A ; I _B = -0.8 A			-1	V
		D44H8,11	I _C = -8A ; I _B = -0.4 A				
V _{BE(sat)}	Base-Emitter Saturation Voltage		I _C = -8A ; I _B = -0.8 A			-1.5	V
I _{CES}	Collector Cutoff Current		V _{CE} =Rated V _{CEO} ;			-10	μ A
I _{EBO}	Emitter Cutoff Current		V _{EB} = -5V; I _C = 0			-100	μ A
h _{FE-1}	DC Current Gain	D44H10	I _C = -2A ; V _{CE} = -1V	35			
		D44H8,11					
h _{FE-2}	DC Current Gain	D44H10	I _C = -4A ; V _{CE} = -1V	20			
		D44H8,11					
C _{OB}	Output Capacitance		V _{CB} = -10V, f= 0.1MHz		130		pF
f _T	Current-Gain—Bandwidth Product		I _C =-0.5A; V _{CE} =-10V; f _{test} =20MHz		50		MHz

Switching Times

t _s	Storage Time	I _C = -5A; I _{B1} = -I _{B2} = -0.5A V _{CC} = 20V		0.5		μ s
t _f	Fall Time			0.14		μ s

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